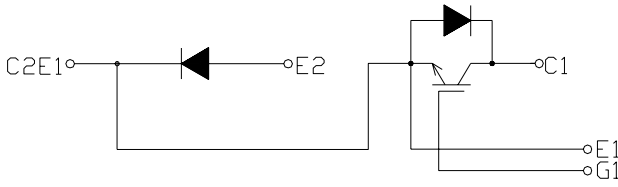


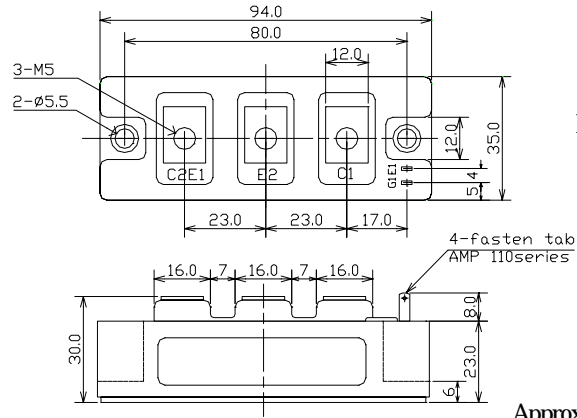
# IGBT MODULE Chopper 100A 1200V

# PCHMB100B12A

## CIRCUIT



## OUTLINE DRAWING



2-fasten- tab No 110

Dimension(mm)

Approximate Weight : 220g

## MAXIMUM RATINGS (Tc=25°C)

Item	Symbol	PCHMB100B12A	Unit
Collector-Emitter Voltage	V <sub>CES</sub>	1200	V
Gate - Emitter Voltage	V <sub>GES</sub>	+/- 20	V
Collector Current	DC	I <sub>C</sub>	100
	1 ms	I <sub>C</sub>	200
Collector Power Dissipation	P <sub>C</sub>	500	W
Junction Temperature Range	T <sub>j</sub>	-40 to +150	°C
Storage Temperature Range	T <sub>sg</sub>	-40 to +125	°C
Isolation Voltage (Terminal to Base AC, 1 min.)	V <sub>ISO</sub>	2500	V
Mounting Torque	Module Base to Heat sink	F <sub>TOR</sub>	2.04
	Bus Bar to Main Terminals		
			Nom

## ELECTRICAL CHARACTERISTICS (Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Emitter Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V	-	-	2.0	mA
Gate-Emitter Leakage Current	I <sub>GES</sub>	V <sub>GE</sub> =+/- 20V, V <sub>CE</sub> =0V	-	-	1.0	µA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =100A, V <sub>GE</sub> =15V	-	1.9	2.4	V
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	4.0	-	8.0	V
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> =10V, V <sub>GE</sub> =0V, f=1MHz	-	8300	-	pF
Switching Time	Rise Time	t <sub>r</sub>	-	0.25	0.45	µs
	Turn-on Time	t <sub>on</sub>	-	0.40	0.7	
	Fall Time	t <sub>f</sub>	-	0.25	0.35	
	Turn-off Time	t <sub>off</sub>	-	0.80	1.10	

## FREE WHEELING DIODES RATINGS & CHARACTERISTICS (Tc=25°C)

Item	Symbol	Rated Value	Unit
Forward Current	DC	I <sub>F</sub>	100
	1 ms	I <sub>FM</sub>	200

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =100A, V <sub>GE</sub> =0V	-	1.9	2.4	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =100A, V <sub>GE</sub> =-10V, di/dt=200A/µs	-	0.2	0.3	µs

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Impedance	IGBT	Junction to Case	-	-	0.24	°C/W
	DIODE		-	-	0.42	

Fig.1- Output Characteristics (Typical)

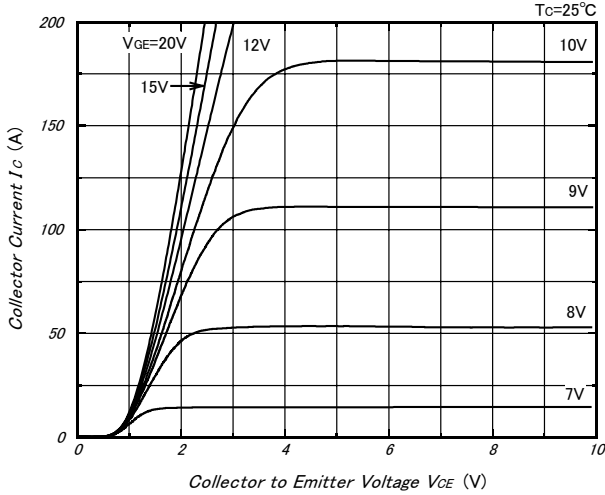


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

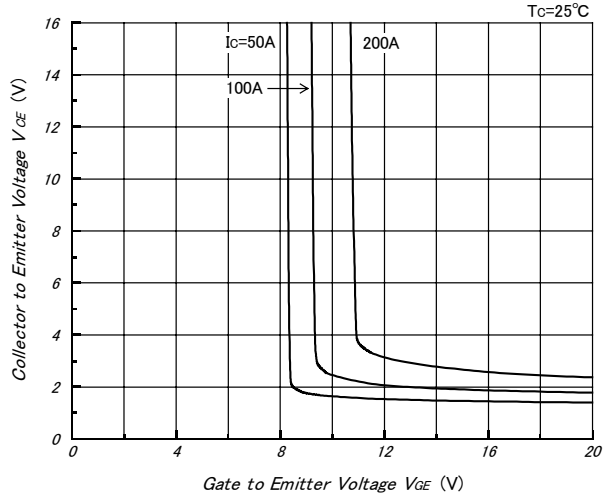


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

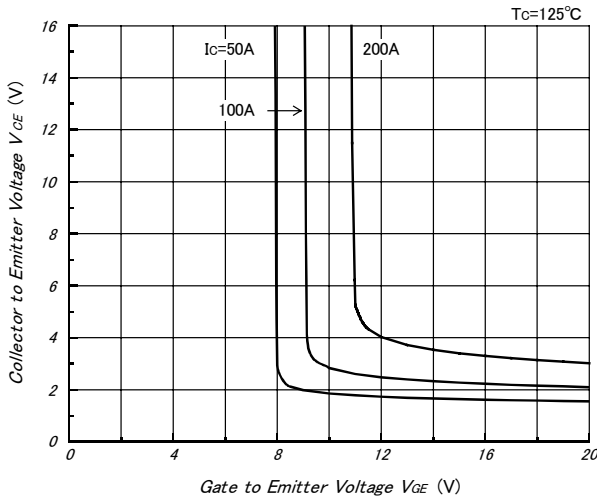


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

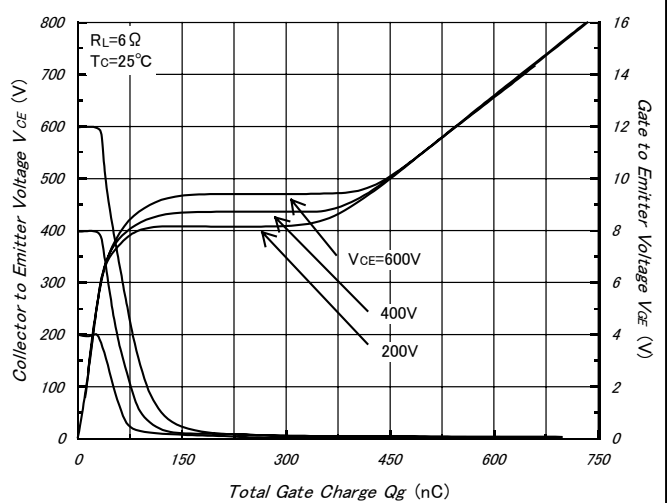


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

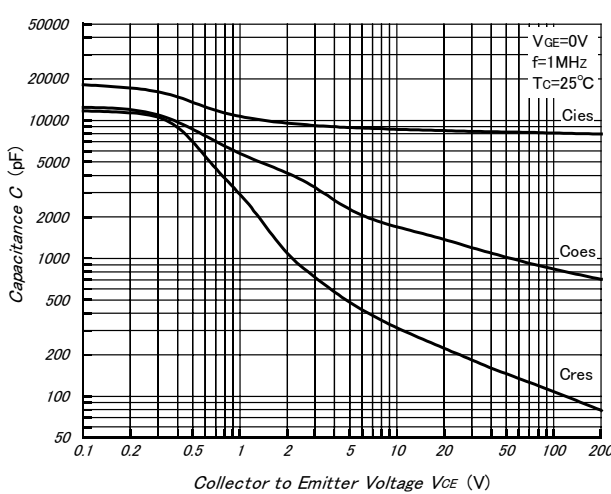


Fig.6- Collector Current vs. Switching Time (Typical)

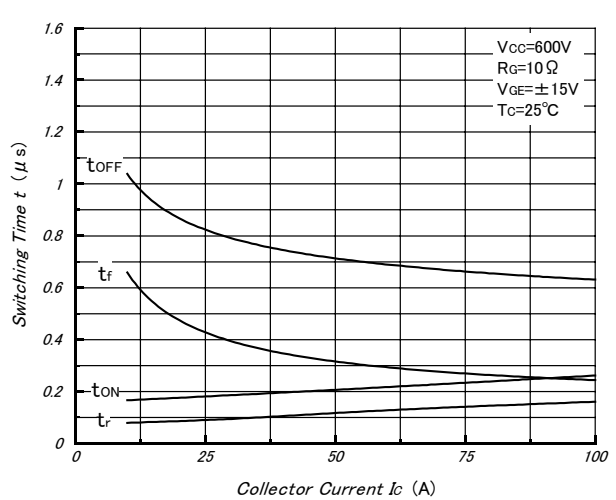


Fig.7- Series Gate Impedance vs. Switching Time (Typical)

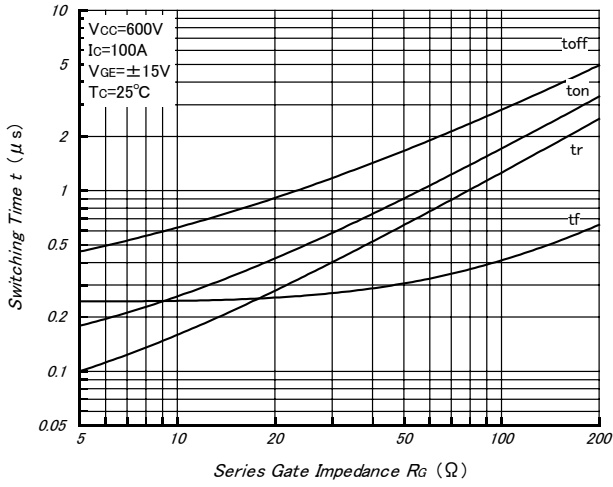


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

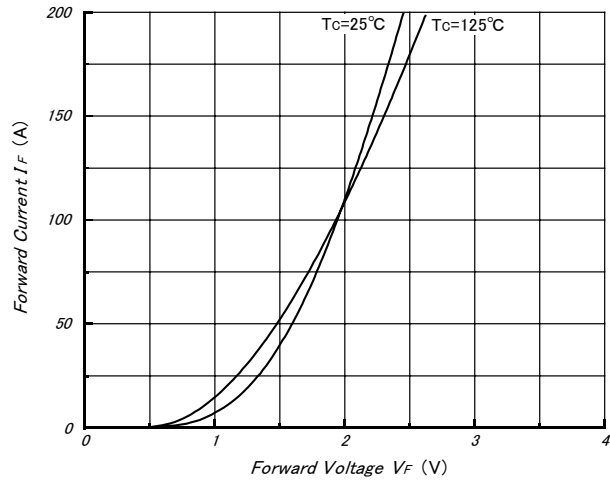


Fig.9- Reverse Recovery Characteristics (Typical)

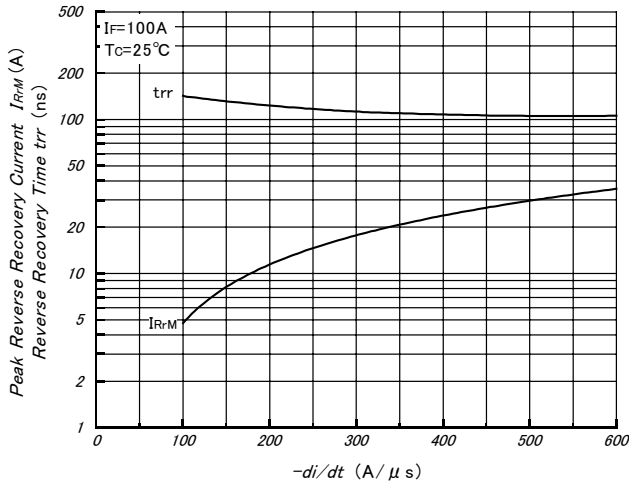


Fig.10- Reverse Bias Safe Operating Area

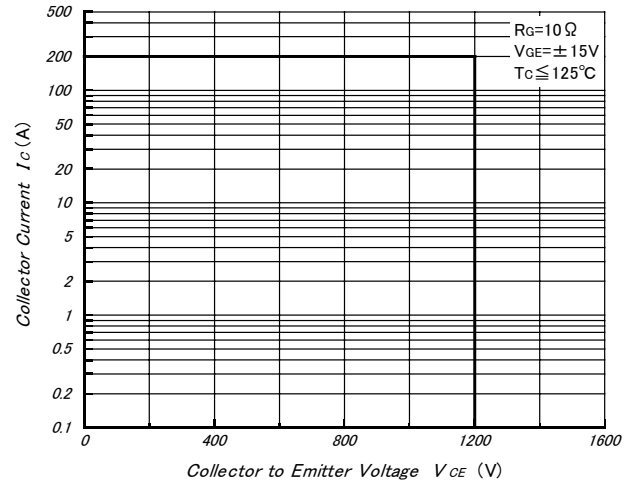


Fig.11- Transient Thermal Impedance

